

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	48675	(semiconductor) with (crystal crystalline single adj crystal)	US-PGPUB; USPAT	OR	OFF	2005/08/22 09:04
L2	86477	(semiconductor silicon) with (crystal crystalline single adj crystal)	US-PGPUB; USPAT	OR	OFF	2005/08/22 09:11
L3	6516	( top\$1gate\$2 top adj gate\$2)	US-PGPUB; USPAT	OR	OFF	2005/08/22 09:26
L4	852309	(lcd electroluminescent display\$2 soi silicon\$1on\$1insulator\$2 silicon adj2 insulator\$2 tft thin adj film adj transistor\$2)	US-PGPUB; USPAT	OR	OFF	2005/08/22 09:01
L5	110268	(base underl\$4 undercoat\$4) with (pattern\$4 etch\$4 taper tapering tapered)	US-PGPUB; USPAT	OR	OFF	2005/08/22 08:55
L6	389	2 and 3 and 4 and 5	US-PGPUB; USPAT	OR	OFF	2005/08/22 09:27
L7	134	(aluminum near2 oxide "Al.sub.2O.sub.3" aluminum adj nitride adj oxide "AlN.sub.xO.sub.1-x" nitride near2 aluminum "AlN.sub.x" AlSiON LaSiON ((aluminum) near2 (rare adj earth)) AlSiON LaSiON boron near2 nitride)and 6	US-PGPUB; USPAT	OR	OFF	2005/08/22 08:56
L8	84919	(semiconductor silicon) with (crystal crystalline single adj crystal)	EPO; JPO; DERWENT	OR	OFF	2005/08/22 09:01
L9	1004	( top\$1gate\$2 top adj gate\$2)	EPO; JPO; DERWENT	OR	OFF	2005/08/22 09:01
L10	1266072	(lcd electroluminescent display\$2 soi silicon\$1on\$1insulator\$2 silicon adj2 insulator\$2 tft thin adj film adj transistor\$2)	EPO; JPO; DERWENT	OR	OFF	2005/08/22 09:01
L19	1	"5965916".pn. and "3"	US-PGPUB; USPAT	OR	OFF	2005/08/22 09:10
L21	5745	257/72 257/347 257/353 438/151 438/149.ccls.	US-PGPUB; USPAT	OR	OFF	2005/08/22 09:15
L22	133	6 and 21	US-PGPUB; USPAT	OR	OFF	2005/08/22 09:15
L23	6527	( top\$1gate\$2 top adj gate\$2 non\$1inverted adj gate)	US-PGPUB; USPAT	OR	OFF	2005/08/22 09:27
L24	389	2 and 23 and 4 and 5	US-PGPUB; USPAT	OR	OFF	2005/08/22 09:27